

EAST Search History

EAST Search History (Prior Art)

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|---------------------------------|---|------------------|---------|---------------------|
| L1 | 1 | 12/128260 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 11:36 |
| L2 | 2 | "20030001170" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:35 |
| L3 | 273961 | p-type p adj type | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:38 |
| L4 | 273959 | p adj type | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:39 |
| L5 | 319366 | p near3 type | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:39 |
| L6 | 13742 | 5 with (ohm\$4 ohmic) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:40 |
| L7 | 10453 | 6 with (contact electrode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:40 |
| L8 | 66122 | Gallium adj Nitride GaN | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:41 |

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|-----|---------|---|---|----|----|---------------------|
| L9 | 6073303 | III-V III V | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:43 |
| L10 | 11311 | 9 same compound same nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:43 |
| L11 | 5755 | 8 and 10 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:43 |
| L12 | 1000 | 7 and 11 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:44 |
| L13 | 292488 | barrier with (layer film) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:45 |
| L14 | 4424 | 13 same (direct with contact\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:46 |
| L15 | 4908 | contact adj metal adj (layer film) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:47 |
| L16 | 1067751 | same\$1 with (material metal) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:47 |
| L17 | 29 | 14 and 15 and 16 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:48 |
| L18 | 74605 | bond\$4 with (layer film) with metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:50 |

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|-----|------|-------------------------------|---|----|----|---------------------|
| L19 | 290 | 18 same 7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:50 |
| L20 | 0 | 17 and 19 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:51 |
| L22 | 6251 | "21" with (ohm\$4 ohmic) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/08/27 14:52 |

EAST Search History (I nterference)

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|-------|---------|---|----------------|------------------|---------|------------------|
| L21 | 120935 | p near3 type | USPAT; UPAD | OR | ON | 2010/08/27 14:51 |
| L23 | 6836 | 21 with (ohm\$4 ohmic) | USPAT; UPAD | OR | ON | 2010/08/27 14:52 |
| L24 | 4519 | 23 with (contact electrode) | USPAT; UPAD | OR | ON | 2010/08/27 14:52 |
| L25 | 19001 | Gallium adj Nitride GaN | USPAT; UPAD | OR | ON | 2010/08/27 14:53 |
| L26 | 1552773 | III-V III V | USPAT; UPAD | OR | ON | 2010/08/27 14:53 |
| L27 | 191774 | 26 same compound | USPAT; UPAD | OR | ON | 2010/08/27 14:53 |
| L28 | 3790 | 27 same nitride | USPAT; UPAD | OR | ON | 2010/08/27 14:54 |
| L29 | 105172 | barrier with (layer film) | USPAT; UPAD | OR | ON | 2010/08/27 14:54 |
| L30 | 2207 | 29 same (direct with contact\$4) | USPAT; UPAD | OR | ON | 2010/08/27 14:55 |
| L31 | 2234 | contact adj metal adj (layer film) | USPAT; UPAD | OR | ON | 2010/08/27 14:55 |
| L32 | 0 | 28 and 30 and 31 | USPAT; UPAD | OR | ON | 2010/08/27 14:56 |

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